

TD3163

Capabilities Data Sheet

Solar Array Bypass Diode

Features

- Ultra Thin Construction
- Low leakage reverse current
- Low forward voltage drop
- Die metallization is solderable or weldable
- Passivated metallization will not degrade in humidity
- Space Level Quality

20 Volts
2.0 Amp

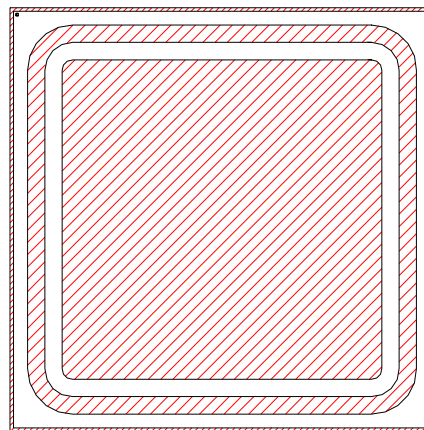
Applications

- Bypass diode designed for Solar Cell protection
- Extreme Temperature Cycling environments
- Exposed Solar Array surface mount

Electrical Characteristics @ 25°C

SYMBOL	CHARACTERISTIC	CONDITIONS	MAX	UNITS
IR	Reverse (Leakage) Current	VR = 2 Vdc	5	uAmps
VF	Forward Voltage	IF = 2.0 A pulse test pw=300ms, d/c<2%	750	mVolts
BVR	Breakdown Voltage	IR = 100 uA	(min) 50	Volts

Mechanical Outline



QCI Testing

- Bond Pull
- Temperature Shock
- High Temperature Reverse Bias
- Burn-In
- Humidity

Chip Dimensions
 0.16" x 0.16" x 0.003"